

9097250 TOSHIBA (DISCRETE/OPTO)

56C 77559 DT-33-09

2SC2562

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

HIGH CURRENT SWITCHING APPLICATIONS.

FEATURES:

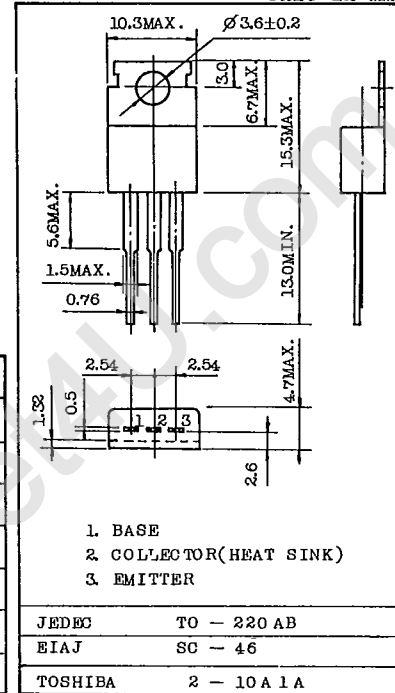
- Low Collector Saturation Voltage :
 $V_{CE(sat)}=0.4V$ (Max.) (at $I_C=3A$)
- High Speed Switching Time : $t_{stg}=1.0\mu s$ (Typ.)
- Complementary to 2SA1012.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	5	A
Collector Power Dissipation (Tc=25°C)	P_C	25	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

INDUSTRIAL APPLICATIONS

Unit in mm



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	50	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=1V, I_C=1A$	70	-	240	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=3A$	30	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	-	0.2	0.4	V
	Base-Emitter	$V_{BE(sat)}$	-	0.9	1.2	
Transition Frequency	f_T	$V_{CE}=4V, I_C=1A$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	80	-	pF
Switching Time	Turn-on Time	t_{on}	-	0.1	-	μs
	Storage Time	t_{stg}	-	1.0	-	
	Fall Time	t_f	-	0.1	-	

Note : $h_{FE(1)}$ Classification 0 : 70~140, Y : 120~240

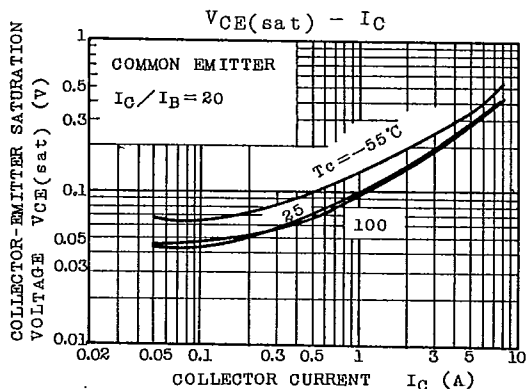
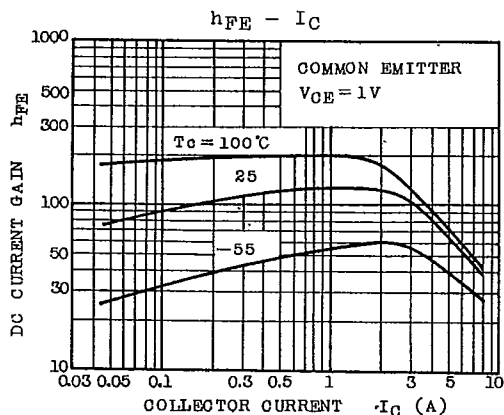
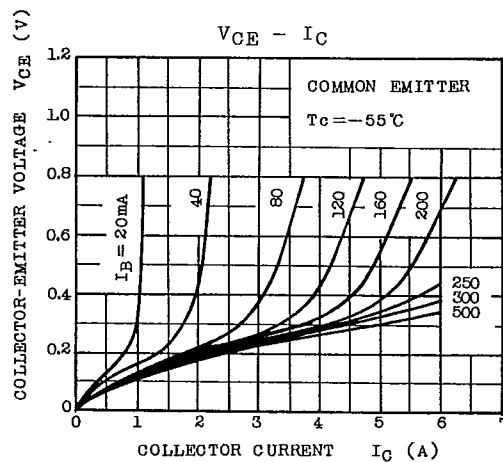
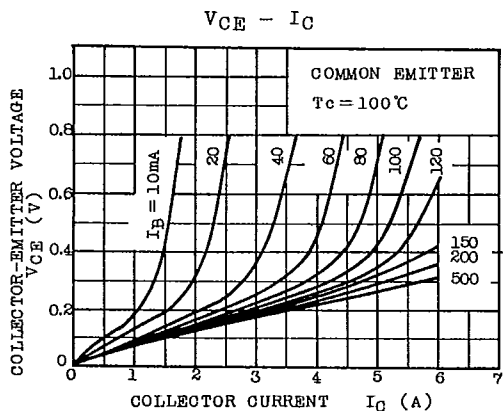
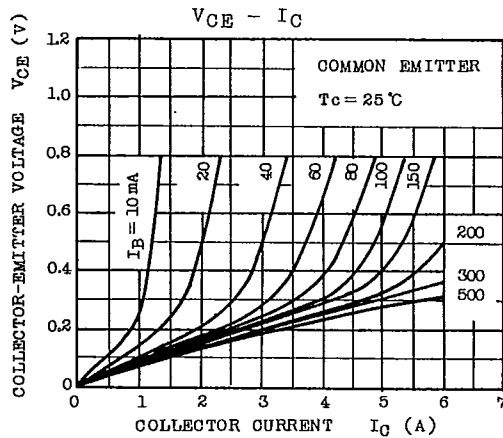
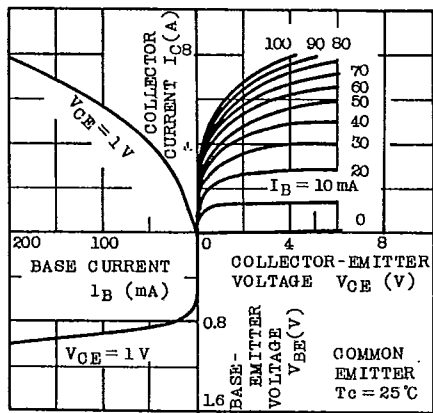
20 μs INPUT I_{B1} I_{B2} OUTPUT $V_{CO} = 30V$

DUTY CYCLE $\leq 1\%$

TOSHIBA CORPORATION

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STATIC CHARACTERISTICS



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